ABSTRACT

Embodiments of the present disclosure provide a semiconductor structure and a method for manufacturing the same. The semiconductor structure includes: a substrate provided with a device region, a first isolation region, and a second isolation region disposed between the device region and the first isolation region. The second isolation region is further provided with a first semiconductor material region adjacent to the first isolation region. In the semiconductor structure according to the embodiments of the present disclosure, by retaining a portion of the semiconductor material region in the isolation region adjacent to the device region, dimensional variations between the device region and the isolation region caused by differences in pattern density are compensated.

[FIG. 10]